# **IrDA SIR Integrated Transceiver**

#### Description

The TFDS2000 is an infrared transceiver for data communication systems. The transceiver is compatible to the IrDA standard which allows data rates up to 10 MBit/s.

Features

- Compatible to IrDA standard
- SMD side view
- Low profile (height = 5.6 mm max.)
- High efficiency, high speed emitter
- Fast photo pin detector diode



TEMIC's integrated IrDA receiver and driver circuit U2532B.

The TFDS2000 enables optimum operation with

Pin description:

- 1: IRED anode
- 2: NC
- 3: Pin diode: cathode
- 4: NC
- 5: Pin diode: anode
- 6: NC
- 7: NC
- 8: IRED cathode

#### **Absolute Maximum Ratings**

Reference point Pin 4, unless otherwise specified

Parameter	Test Conditions	Symbol	Value	Unit
Reverse voltage pin photo diode emitter diode		V <sub>R</sub> V <sub>R</sub>	60 6	V V
Forward currents pin photo diode emitter diode	Average, cw Pulse (<90 μs, t <sub>on</sub> <20%) Peak (<2 μs, t <sub>on</sub> <10%)	$\begin{array}{c} I_{F} \\ I_{IRED}(DC) \\ I_{IRED}(RP) \\ I_{IRED}(PK) \end{array}$	50 100 500 1000	mA mA mA mA
Power dissipation	See figure 3	P <sub>tot</sub>	200	
Junction temperature		TJ	125	°C
Ambient temperature Range (operating)		T <sub>amb</sub>	0 to 70	°C
Soldering temperature	See figure 11 introductory text IrDA Design Guide		230 (typ. 215)	°C

## **Basic Characteristics**

 $T_{amb} = 25^{\circ}C$ , unless otherwise specified

Parameter	Test Conditions	Symbol	Min.	Тур.	Max.	Unit
Photo pin diode	· ·					·
Breakdown voltage	$I_R = 100 \ \mu A, E = 0$	V <sub>(BR)</sub>	32			V
Spectral sensitivity	$\lambda = 870 \text{ nm}$	sλ		0.5		A/W
Light reverse current	$V_{R} = 5 V$ $E = 1 W/m^{2}$ $\lambda = 870 \text{ nm}$	Ira		4.4		uA
Temperature coefficient of light reverse current		TK <sub>Ira</sub>		-0.1		%/K
Spectral bandwidth		λ <sub>0.5</sub>		790 to 1050		nm
Dark reverse current	$V_{\rm R} = 10  \rm V,  \rm E = 0$	I <sub>ro</sub>		0.1	30	nA
Rise time, fall time	$\label{eq:VR} \begin{array}{l} V_R = 5 \ V, \ R_L = 1 \ k\Omega, \\ E = 1 \ W/m^2 \\ \lambda = 870 \ nm \end{array}$			100		ns
Junction capacitance	$V_{R} = 5 V, f = 1 MHz$	C <sub>jd</sub>		5.8		pF
Transmitter						
Forward voltage	$I_F = 100 \text{ mA},$ $t_p = 20 \text{ ms}$	V <sub>F</sub>		1.35	1.6	V
Forward voltage	$I_F = 600 \text{ mA},$ $t_p = 100  \mu \text{s}$	V <sub>F</sub>		2.2	2.8	V
Reverse current	$\dot{V}_{R} = 5 V, E = 0$	I <sub>R</sub>			10	μA
Junction capacitance	$V_{R} = 0 V, f = 1 MHz$	C <sub>je</sub>		160		pF
Temperature coefficient of forward voltage V <sub>F</sub>		TK <sub>VF</sub>		-1.3		mV/K
Output radiant intensity, $\alpha = \pm 15^{\circ}$	$I_F = 300 \text{ mA}$	I <sub>e</sub>		100		mW/sr
Angle of half intensity		α		±24		0
Peak wavelength of emis- sion		λp	850		900	nm
Half width of emission spectrum				60		nm
Temperature coefficient of peak wavelength λp		$TK_{\lambda p}$		+0.2		nm/K
Optical rise/fall time	$I_{\rm F} = 100 \ {\rm mA}$	t <sub>r</sub> , t <sub>f</sub>		30		ns
Temperature coefficient of intensity I <sub>e</sub>		TK <sub>Ie</sub>		-0.35		%/K



#### **Recommended SMD pads for the transceiver TFDS2000 Dimensions in mm**



Figure 1.



Figure 2. Current derating as a function of ambient temperature condition duty cycle <20%

### **Dimensions in mm**



# Preliminary Information

**TELEFUNKEN Semiconductors** Rev. A1, 12-Mar-96

#### **Ozone Depleting Substances Policy Statement**

It is the policy of **TEMIC TELEFUNKEN microelectronic GmbH** to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**TEMIC TELEFUNKEN microelectronic GmbH** semiconductor division has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**TEMIC** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use TEMIC products for any unintended or unauthorized application, the buyer shall indemnify TEMIC against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

TEMIC TELEFUNKEN microelectronic GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423